

Features

- 650-Volt Schottky Rectifier
- Zero Reverse Recovery Current
- Zero Forward Recovery Voltage
- High-Frequency Operation
- Temperature-Independent Switching Behavior
- Extremely Fast Switching
- Positive Temperature Coefficient on V_F

Benefits

- Replace Bipolar with Unipolar Rectifiers
- Essentially No Switching Losses
- Higher Efficiency
- Reduction of Heat Sink Requirements
- Parallel Devices Without Thermal Runaway

Applications

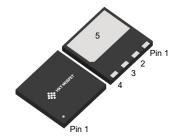
- Switch Mode Power Supplies
- Power Factor Correction
- Motor Drives



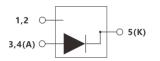




Part Number	Package	Qty(PCS)	
WNSC08650T6J	DFN8X8B	3000	



DFN8X8B



Maximum Ratings (T_C = 25 °C unless otherwise specified)

Symbol	Parameter	Value	Unit	Test Conditions
V _{RRM}	Repetitive Peak Reverse Voltage	650	V	
V _{RSM}	Surge Peak Reverse Voltage	650	٧	
I _F	Continuous Forward Current	23.1 10.8 8	А	T _c =25°C T _c =135°C T _c =150.5°C
I _{FRM}	Repetitive Peak Forward Surge Current	30	А	T _c =25°C, t _p = 10 ms, Half Sine Wave
I _{FSM}	Non-Repetitive Peak Forward Surge Current	60	А	T_c =25°C, t_p = 10 ms, Half Sine Wave
P _{tot}	Power Dissipation	93 40	W	T _c =25°C T _c =110°C
T_{J} , T_{stg}	Operating Junction and Storage Temperature	-55 to +175	°C	
∫i²dt	i ² dt value	18	A ² s	T_c =25°C, t_p = 10 ms, Half Sine Wave



Electrical Characteristics

Symbol	Parameter	Min.	Тур.	Max.	Unit	Test Conditions
V _{DC}	DC Blocking Voltage	650			٧	
V _F	Forward Voltage		1.42 1.88	1.7 2.5	V	I _F = 8 A T _J =25°C I _F = 8 A T _J =175°C
I _R	Reverse Current		0.12 0.91	50 100	μΑ	V _R = 650 V T _J =25°C V _R = 650 V T _J =175°C
Q _c	Total Capacitive Charge		21		nC	V _R = 400 V T _J = 25°C
С	Total Capacitance		395 42 41		pF	V _R = 0 V, T _J = 25°C, f = 1 MHz V _R = 200 V, T _J = 25°C, f = 1 MHz V _R = 400 V, T _J = 25°C, f = 1 MHz
E _c	Capacitance Stored Energy		5		μJ	V _R = 400 V

Thermal Characteristics

Symbol	Parameter	Тур.	Unit
R _{eJC}	Thermal Resistance from Junction to Case	1.61	°C/W

Typical Performance

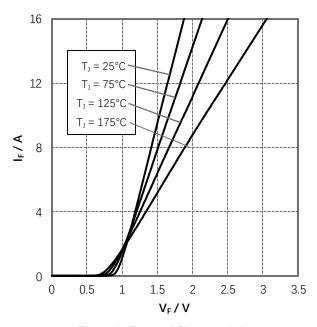


Figure 1. Forward Characteristics

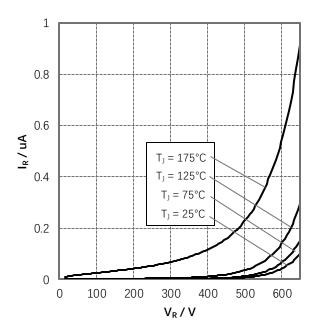


Figure 2. Reverse Characteristics

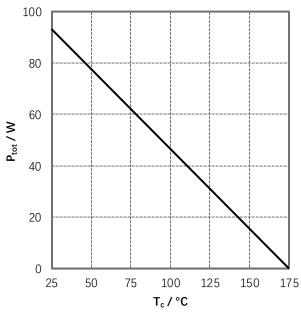


Figure 3. Power Derating

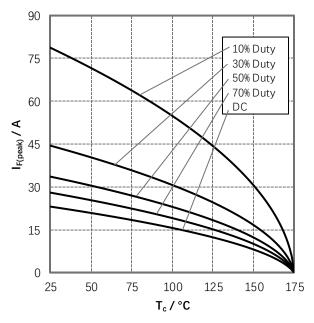


Figure 4. Current Derating

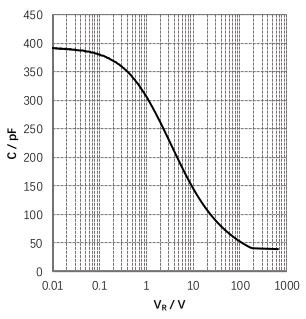


Figure 5. Capacitance vs. Reverse Voltage

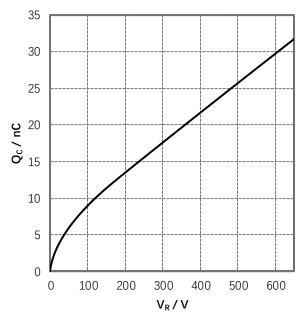


Figure 6. Total Capacitance Charge vs. Reverse Voltage

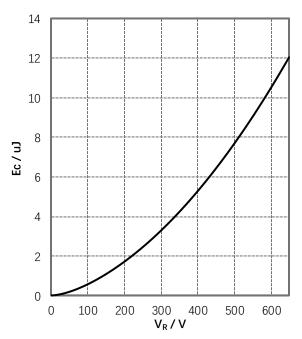


Figure 7. Capacitance Stored Energy

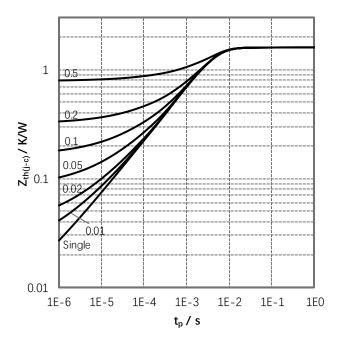
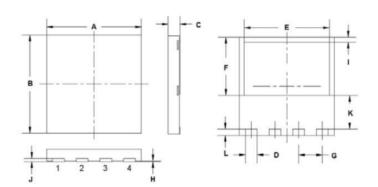


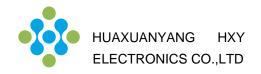
Figure 8. Transient Thermal Impedance

Package Information DFN8X8B



Unit: mm

Dimension	Min.	Max.
Α	7.90	8.10
В	7.90	8.10
С	0.75	0.95
D	0.90	1.10
E	7.10	7.30
F	4.65	4.85
G	1.80	2.20
Н	0.00	0.05
1	0.30	0.50
J	0.10	0.30
K	2.65	2.85
L	0.40	0.60



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